



# **ISC Silicon NPN Power Transistor**

# **DESCRIPTION**

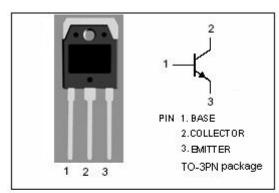
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 400V(Min)
- · High Switching Speed
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

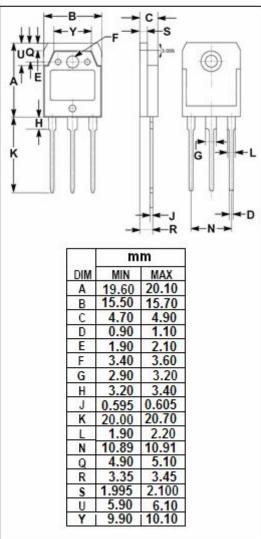
## **APPLICATIONS**

· Designed for high voltage, high speed and high power switching applications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base voltage	10	V
lc	Collector Current-Continuous	10	А
Ісм	Collector Current-Peak	20	А
I <sub>B</sub>	Base Current-Continuous	5	А
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C	80	W
TJ	Junction Temperature	150	$^{\circ}$ C
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C







# isc Silicon NPN Power Transistor

2SC3365

## **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 0.2A; R <sub>BE</sub> = ∞; L= 100mH	400			V	
V <sub>CEX(SUS)</sub>	Collector-Emitter Sustaining Voltage	$I_{C}$ = 10A; $I_{B1}$ = 2A; $I_{B2}$ = -0.6A; $V_{BE}$ = -5V; L= 180 $\mu$ H; Clamped	400			V	
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	10			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A			1.0	V	
$V_{\text{BE}(sat)}$	Base-Emitter Saturation Voltage	Ic= 5A; I <sub>B</sub> = 1A			1.5	V	
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 400V; I <sub>E</sub> = 0			50	μА	
ICEO	Collector Cutoff Current	V <sub>CE</sub> = 350V; R <sub>BE</sub> = ∞			50	μ <b>А</b>	
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	12				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 5V	5				
Switching times							

#### Switching times

t <sub>on</sub>	Turn-on Time			1.0	μS
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 10A, I <sub>B1</sub> = -I <sub>B2</sub> = 2A; V <sub>CC</sub> ≈ 150V		2.5	μς
t <sub>f</sub>	Fall Time			1.0	μS

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